

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	198878	chemical vapor deposition or \$2cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 10:55
S2	5303	S1 and (ammonia or "nh.sub.3") same (silane or "sih.sub.4") same (nitride or SiN\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 16:20
S3	554	S1 and ((ammonia or "nh.sub.3") same (silane or "sih.sub.4") same (nitride or SiN\$6) same (nitrogen or "n.sub.2") same sccm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 11:44
S4	1195	S1 and ((ammonia or "nh.sub.3") same (silane or "sih.sub.4") same (nitride or SiN\$6) same (nitrogen or "n.sub.2") and sccm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 11:44
S5	189	S4 and (showerhead or shower head)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 11:45
S6	10	("5441768").URPN.	USPAT	ADJ	ON	2005/09/21 11:55
S7	19	("3874919" "4110899" "4268321" "4333964" "4398992" "4729816" "5306946" "5441768" "5472906" "5679600").PN. OR ("6090686").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/09/21 12:03
S8	11	("5273920").PN. OR ("5441768").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/09/21 12:23
S9	22	("3549411" "4342617" "4688078" "4851361" "5166556" "5382551" "5422300" "5468689" "5541436" "5670432" "5683922" "5707889" "5739066" "5851879" "5939763" "6051511" "6090686" "6093956" "6110784" "6174644" "6297130").PN. OR ("6703690").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/09/21 12:27

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S10	19	("4210470" "4262631" "4532695" "4546540" "4645683" "4836885" "5045346" "5075743" "5094984" "5238869" "5360754").PN. OR ("5468689").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/09/21 12:47
S11	4	("4563367" "5134092" "5468689" "5539154").PN. OR ("6348419").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/09/21 12:57
S12	25	("3549411" "3842490" "4181564" "4239587").PN. OR ("4342617").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/09/21 13:16
S13	4135	S1 and (ammonia or "nh.sub.3") same (silane or "sih.sub.4") same (nitride or SiN\$6) and ((graded or layer\$2 or discontinuity or junction) with nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 13:18
S14	189	S1 and (ammonia or "nh.sub.3") same (silane or "sih.sub.4") same (nitride or SiN\$6) and ((graded or discontinuity or junction) with nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 14:24
S15	2	"5629043".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 14:55
S16	2	"4395438".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 14:55
S18	775	bird\$1s beak	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 15:15
S19	372	S18 and silicon nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 15:16
S20	18	S19 and ((silane or "sih.sub.4") same (ammonia or "nh.sub.3"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 15:16

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S21	4767	(ammonia or "nh.sub.3") same (silane or "sih.sub.4") same (silicon nitride or "si.sub.3" "n.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 16:21
S22	4062	S21 and (chemical vapor deposition or \$2cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 16:22
S23	50	S22 and ((showerhead or shower head or distribution plate) same heater)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 16:23
S24	36	S23 and ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/21 16:33
S25	2	"5336640".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/22 09:55
S26	2	"5872655".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/22 11:33
S27	2333	427/255.28,255.393,255.394,255.7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/22 11:35
S28	547	S27 and (silicon nitride or "si.sub.3" "n.sub.4" or "si.sub.3n.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/22 11:36
S29	936	(chemical vapor deposition or \$2cvd) same (ammonia or "nh.sub. 3") same (\$4silane or "sih.sub.4") same ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:43
S30	450	(chemical vapor deposition or \$2cvd) same (ammonia or "nh.sub. 3") with (\$4silane or "sih.sub.4") with ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:49

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S31	279	S29 and second near3 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:04
S32	94	S30 and second near3 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:04
S33	33	("5041888").URPN.	USPAT	ADJ	ON	2006/06/05 11:36
S34	13	S33 and second near3 nitride	USPAT	ADJ	ON	2006/06/05 11:37
S35	10	S34 and ratio	USPAT	ADJ	ON	2006/06/05 11:37
S36	0	(chemical vapor deposition or \$2cvd) same (ammonia or "nh.sub. 3") with (\$4silane or "sih.sub.4") with ratio same graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:43
S37	2	(chemical vapor deposition or \$2cvd) same (ammonia or "nh.sub. 3") same (\$4silane or "sih.sub.4") same ratio same graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:44
S38	6	(chemical vapor deposition or \$2cvd) and (ammonia or "nh.sub. 3") same (\$4silane or "sih.sub.4") same ratio same graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:47
S39	2188	(bi or two or dual) layer\$3 with silicon nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:48
S40	447	S39 same (chemical vapor deposition or \$2cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 11:49
S41	12	S40 and (ammonia or "nh.sub.3") with (\$4silane or "sih.sub.4") with ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/05 12:28
S42	7	semiconductor same trench with bottom with side with top with thick\$4 same deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/06 10:38

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S43	2039	semiconductor same step coverage same deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/06 10:39
S44	407	S43 same ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/06 10:43
S45	281	semiconductor same step coverage with ratio same deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/06 10:39
S46	11	S43 same ratio same silicon nitride and (chemical vapor deposition or \$2cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/06 10:43